

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5928	photonic ADJ2 crystal\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:01
L2	2530325	charges carriers electrons holes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:02
L3	2397	L1 AND L2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:03
L4	1325308	(holes columns) SAME (form\$3 coat\$3 layer\$3 cover\$3 insulat\$3 semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:05
L5	1627	L3 AND L4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:05
L6	124	L5 AND (insulators insulaton)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:06
L7	393	L3 AND (insulators insulaton insulating) AND (holes columns pillars)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:08
L8	88113	insulat\$4 WITH (holes columns pillars)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:09
L9	117	L1 AND L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:11
L10	5125	photonic ADJ crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:47

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L11	149617	silicon NEAR4 semiconductor\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:14
L12	165395	plurality NEAR2 holes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:13
L13	1191	hole SAME pitch SAME radius	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:13
L14	18359	poly\$1silicon NEAR4 semiconductor\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:14
L15	3553	charge NEAR2 modulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:15
L16	24	L10 AND L11 AND L14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:19
L17	1	L10 AND L11 AND L12 AND L13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:19
L18	1	L10 AND L11 AND L12 AND L13 AND L14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:19
L19	45	method\$1 SAME beam\$1 SAME photonic ADJ crystal SAME lattice	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:22
L20	61	silicon NEAR2 semiconductor SAME lattice SAME holes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:23

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L21	1	L19 AND L18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:23
L22	7266	poly\$1silicon NEAR2 semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:24
L23	50630	band adj. gap band\$1gap	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:25
L24	269	L22 AND L23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:27
L25	16	L1 AND L24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:28
L26	2866	modulat\$3 SAME (band ADJ gap band\$1gap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:29
L27	351	L1 AND L26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:30
L28	2	L20 AND L27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:34
L29	32205	optical SAME transmitter SAME receiver	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:35
L30	43	L5 AND L29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:36

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L31	8	L30 AND L11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:38
L32	14	SALIB-Michael-S.IN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:41
L33	6	(Intel ADJ Corporation).AS. AND (photonic ADJ crystal\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:42
L34	3096	257/98.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:44
L35	1619	359/245.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:45
L36	613	359/298.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:45
L37	256	359/315.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:45
L38	189	359/320.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:45
L39	280	359/322.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:46
L40	2471	385/129.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:46

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L41	1470	385/130.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:46
L42	1315	385/131.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:46
L43	993	385/132.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:47
L44	464	359/321.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/23 10:47
L45	1	((photonic ADJ crystal) AND (silicon NEAR4 semiconductor\$1) AND (plurality NEAR2 holes) AND (hole SAME pitch SAME radius) AND (poly\$1silicon NEAR4 semiconductor\$1) AND (charge NEAR2 modulat\$3)).CLM.	US-PGPUB; USPAT	OR	OFF	2007/07/23 10:50
L46	0	((photonic ADJ crystal) AND (silicon NEAR4 semiconductor\$1) AND (plurality NEAR2 holes) AND (hole SAME pitch SAME radius) AND (poly\$1silicon NEAR4 semiconductor\$1) AND (charge NEAR2 modulat\$3)).CLM. NOT "20050185966".PN.	US-PGPUB; USPAT	OR	OFF	2007/07/23 10:50